



# cmos028fdsoi Technology

## EGLVT Power Switch models

### DK1.2\_RF\_mmW

#### Comparison with DK1.1\_RF\_mmW model(s)

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## General information on EGLVT Power Switch models

- Maximum supply voltage is 1.15 V.
- Validity domain is defined as follows:
  - ✓ Drawn gate length varies from 100 nm to 100 nm.
  - ✓ Drawn transistor width varies from 55.35  $\mu\text{m}$  to 55.35  $\mu\text{m}$ .
  - ✓ Device temperature varies from -40 °C to 125 °C.

## Output parameters definitions

### ● Model(s): eglvtpspfet

- ✓  $V_{t\_lin}$  : Threshold voltage defined as  $V_{gs}$  value for which drain current is  $70e-9 * M * 1 * W / (1 * L + 0 + 1 * p\_la)$  at  $V_{ds} = 0.05V$ .
- ✓  $G_{m\_ana}$  : Drain transconductance at  $I_{ds} = 5e-6 * M * W / L$ ,  $V_{ds} = 0.3V$ ,  $f = 100kHz$ .
- ✓  $S_{v@1Hz}$  : Gate noise voltage spectral density at 1Hz,  $V_{gs} = V_{gs\_ana}$ ,  $V_{ds} = 0.3V$
- ✓  $G_{ds\_ana}$  : Drain conductance at  $I_{ds} = 5e-6 * M * W / L$ ,  $V_{ds} = 0.3$ ,  $f = 100k$
- ✓  $F_{t\_ana}$  : Transition frequency at  $I_{ds} = 5e-6 * M * W / L$ ,  $V_{ds} = 0.3V$
- ✓  $V_{gs\_ana}$  :  $V_{gs}$  value for which drain current is  $5e-6 * M * shrink\_iana * W / (shrink\_iana * L + dlshrink\_iana + plashrink\_iana * p\_la)$  at  $V_{ds}=0.3V$ .
- ✓  $C_{dd\_ana}$  : Total drain capacitance at  $I_{ds} = 5e-6 * M * W / L$ ,  $V_{ds} = 0.3V$ ,  $f = 100kHz$ .
- ✓  $I_{lin}$  : Drain current at  $V_{gs} = 1.15V$ ,  $V_{ds} = 0.05V$ .
- ✓  $C_{dg\_ana}$  : Drain-to-Gate transcapacitance at  $I_{ds} = 5e-6 * M * W / L$ ,  $V_{ds} = 0.3V$ ,  $f = 100kHz$ .
- ✓  $I_{offsat}$  : Drain current at  $V_{gs} = -0.83V$ ,  $V_{ds} = v_{ds\_sat}V$ .
- ✓  $V_{tGmmax}$  : Threshold voltage at  $V_{ds} = 0.05$  derived from  $G_m$  max method.
- ✓  $LogI_{off}$  :  $\log_{10}(I_{offsat})$ .
- ✓  $A_{beta}$  :  $\delta G_{mMax} / G_{mMax} * \sqrt{w/L}$
- ✓  $C_{gg\_ana}$  : Total gate capacitance at  $I_{ds} = 5e-6 * M * W / L$ ,  $V_{ds} = 0.3V$ ,  $f = 100kHz$
- ✓  $G_{DC\_ana}$  : Voltage gain at  $I_{ds} = 5e-6 * M * W / L$ ,  $V_{ds} = 0.3V$ ,  $f = 100kHz$
- ✓  $S_{v@th}$  : Gate thermal noise voltage spectral density,  $V_{gs} = V_{gs\_ana}$ ,  $V_{ds} = 0.3V$
- ✓  $I_{sat}$  : Drain current at  $V_{gs} = 1.15V$ ,  $V_{ds} = 1.15V$ .

- ✓  $A_{Id} : \Delta I_d / I_d * \sqrt{W.L}$
- ✓  $A_{Vt} : \Delta V_t * \sqrt{W.L}$
- ✓  $V_{t\_sat}$  : Threshold voltage defined as  $V_{gs}$  value for which drain current is  $70e-9 * M^1 * W / (1 * L + 0 + 1 * p_{la})$  at  $V_{ds} = v_{ds\_satV}$ .

# eglvtpspfet

## Electrical characteristics per geometry

**eglvtpspfet @ w=55.35e-06, l=0.1e-06, nf=3, swshe=0, pre\_layout\_local=1,  
sa=3.96e-6, sb=4.2e-6, sd=1.4e-07, devtype=PT, as=7.3062e-11, ad=7.3062e-11,  
ps=4.482e-05, pd=4.482e-05, vbs=1.15, vdd=1.15, temp=25**

DK1.2\_RF\_mmW wrt DK1.1\_RF\_mmW

	SSF	TT	FFF
Vt_lin [mV]	456.5 0.0mV	398.1 0.0mV	332 0.0mV
Ilin [mA]	0.9 0.0%	1.09 0.0%	1.31 0.0%
Vt_sat [mV]	421.9 0.0mV	363.1 0.0mV	295.9 0.0mV
Isat [mA]	6.32 0.0%	7.78 0.0%	9.34 0.0%
Ioffsat [pA]	28.25 0.0%	80.15 0.0%	321.3 0.0%
LogIoff [log(A)]	-10.55 -0.0%	-10.1 -0.0%	-9.49 -0.0%
VtGmmax [mV]	452 0.0mV	399.6 0.0mV	339 0.0mV
Vgs_ana [mV]	972.5 0.0mV	878.6 0.0mV	783.9 0.0mV
GDC_ana []	1.64 0.0%	2.01 0.0%	2.39 0.0%
GBW_QS [GHz]	2.4 0.0%	3.08 0.0%	3.83 0.0%
Ft_ana [GHz]	25.43 0.0%	28.9 0.0%	32.14 0.0%
Gm_ana [mS]	7.5 0.0%	8.32 0.0%	9.07 0.0%
Gds_ana [mS]	4.58 0.0%	4.15 0.0%	3.79 0.0%
Sv@1Hz [V/√Hz]	3.09e-06 0.0%	4.86e-06 0.0%	7.8e-06 0.0%
Sv@th [V/√Hz]	4.49e-09 0.0%	4.29e-09 0.0%	4.1e-09 0.0%
Cgg_ana [fF]	46.91 0.0%	45.83 0.0%	44.89 0.0%
Cdg_ana [fF]	386.2 0.0%	386.3 0.0%	379.4 0.0%
Cdd_ana [fF]	217.6 0.0%	209.4 0.0%	201.4 0.0%

<b>Avt [mV.μm]</b>	7.33 0.3%	7.37 0.3%	7.41 0.3%
<b>Abeta [%·μm]</b>	0.89 0.6%	0.81 0.6%	0.75 0.6%
<b>AId [%·μm]</b>	1.31 -0.3%	1.2 -0.3%	1.09 -0.3%



# Annex

## Conditions of simulations

The simulations were done with SBenchLSF Alpha using Eldo simulator 2018.3.

- Model eglvtpsfet (DK1.2\_RF\_mmW)

- ✓ Input Parameters

- ✗  $v_{ds\_off} = v_{ds\_sat}$  V
    - ✗  $v_{ds\_cgd} = 0$  V
    - ✗  $v_{ds\_cgg} = 0$  V
    - ✗  $mc\_sens = 0$
    - ✗  $v_{ds\_lin} = 0.05$  V
    - ✗  $i_{vt} = 70e-9$  A
    - ✗  $model\_version = 1.2.d$
    - ✗  $i_{ana} = 5e-6$  A
    - ✗  $v_{ds\_mm} = 50e-3$  V
    - ✗  $ams\_release = 2018.3$
    - ✗  $v_{gs\_stop} = v_{dd}$  V
    - ✗  $dlshrink\_i_{vt} = 0$
    - ✗  $sbenchlsf\_release = Alpha$
    - ✗  $v_{ds\_sat} = 1.15$  V

- ✗ mc\_nsigma = 3
- ✗ shrink\_ivt = 1
- ✗ dlshrink\_tinv = -26e-9
- ✗ vgs\_start = -0.5 V
- ✗ plashrink\_ivt = 1
- ✗ ithslwi = 10e-9 A
- ✗ vds\_ana = 0.3 V
- ✗ vds\_cbd = 0 V
- ✗ vddmax = vdd
- ✗ voffset = 0.2 V
- ✗ mc\_runs = 5000
- ✗ vstep\_ivt = 0.005 V
- ✗ vgs\_off = -0.83 V
- ✗ temp = 25 °C
- ✗ f\_ext = 100k Hz
- ✗ vbs = 1.15 V
- ✗ vdd = 1.15 V
- ✗ shrink\_tinv = 0.9
- ✗ vds\_gmgd = 0.6 V
- ✓ Sweep Parameters
- ✓ Extra parameters
  - ✗ eglvt\_dev = 1
- Model eglvtspfet (DK1.1\_RF\_mmW)
  - ✓ Input Parameters
    - ✗ vds\_off = vds\_sat V

- ✗  $vds\_cgd = 0\text{ V}$
- ✗  $vds\_cgg = 0\text{ V}$
- ✗  $mc\_sens = 0$
- ✗  $vds\_lin = 0.05\text{ V}$
- ✗  $ivt = 70e-9\text{ A}$
- ✗  $model\_version = 1.2.c$
- ✗  $iana = 5e-6\text{ A}$
- ✗  $vds\_mm = 50e-3\text{ V}$
- ✗  $ams\_release = 2018.3$
- ✗  $vgs\_stop = vdd\text{ V}$
- ✗  $dlshrink\_ivt = 0$
- ✗  $sbenchlsf\_release = \text{Alpha}$
- ✗  $vds\_sat = 1.15\text{ V}$
- ✗  $mc\_nsigma = 3$
- ✗  $shrink\_ivt = 1$
- ✗  $dlshrink\_tinv = -26e-9$
- ✗  $vgs\_start = -0.5\text{ V}$
- ✗  $plashrink\_ivt = 1$
- ✗  $ithslwi = 10e-9\text{ A}$
- ✗  $vds\_ana = 0.3\text{ V}$
- ✗  $vds\_cbd = 0\text{ V}$
- ✗  $vddmax = vdd$
- ✗  $voffset = 0.2\text{ V}$
- ✗  $mc\_runs = 5000$
- ✗  $vstep\_ivt = 0.005\text{ V}$

- ✗  $v_{gs\_off} = -0.83 \text{ V}$
- ✗  $temp = 25 \text{ }^{\circ}\text{C}$
- ✗  $f_{ext} = 100\text{k Hz}$
- ✗  $v_{bs} = 1.15 \text{ V}$
- ✗  $v_{dd} = 1.15 \text{ V}$
- ✗  $shrink\_tinv = 0.9$
- ✗  $v_{ds\_gmgd} = 0.6 \text{ V}$
- ✓ Sweep Parameters
- ✓ Extra parameters
  - ✗  $eglv_{t\_dev} = 1$
  - ✗  $gflag\_noisedev\_eglv_{t\_cmos028fdsoi} = 0$